重庆平伟实业股份有限公司
CHONGQING PINGWEI ENTERPRISE CO.,LTD

BAV70

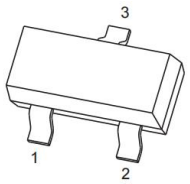
Switching Diode

FEATURE

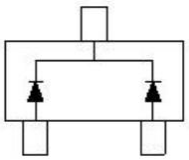
- Fast Switching Speed
- For General Purpose Switching Applictions
- High Conductance
- Low Current Leakage
- Small Outline Surface Mount Package
- RoHS compliant / Green EMC

MARKING: A4

SOT-23



Schematic diagram



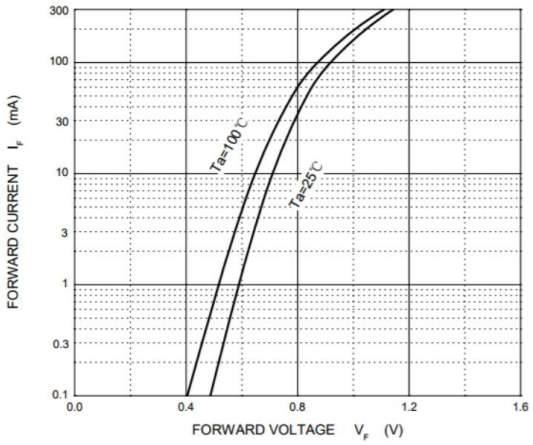
ABSOLUTE MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	75	V
Average Rectified Output Current	I_O	150	mA
Power Dissipation	P_{tot}	350	mW
Peak Forward Surge Current @t=1.0S Non-Repetitive	I_{FSM}	1.0	A
Junction Temperature	T_J	150	℃
Storage Temperature	T_{stg}	-55 to 150	℃
Thermal Resistance	R	357	℃/W

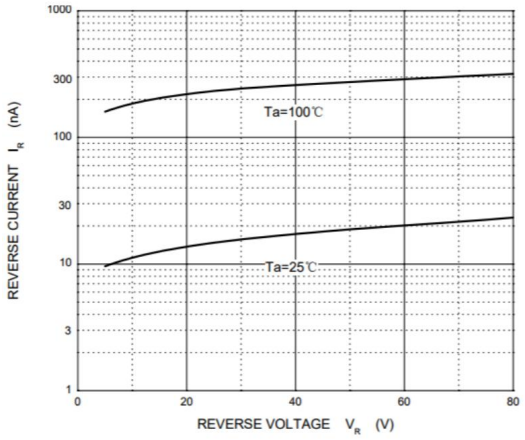
ELECTRICAL CHARACTERISTICS(T_a=25℃ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Forward Voltage	V_F	I_F=1mA			0.715	V
		I_F=10mA			0.855	V
		I_F=50mA			1.00	V
		I_F=150mA			1.25	V
Reverse breakdown voltage	V_R	I_R=100uA	75			V
Reverse voltage leakage current	I_R	V_R=75V			2.5	uA
		V_R=75V Ta=150℃			50	uA
Typical Junction Capacitance	C_J	V_R=0V, f=1.0MHz			2	pF
Reverse recovery time	T_{rr}	I_F= 10mA,V_R=0V, R_L= 100Ω			4	nS

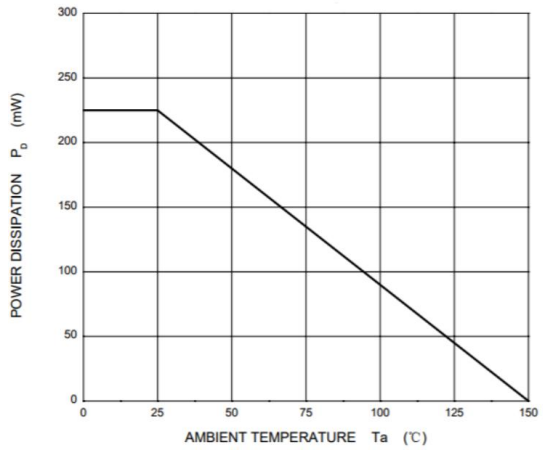
Typical Electrical



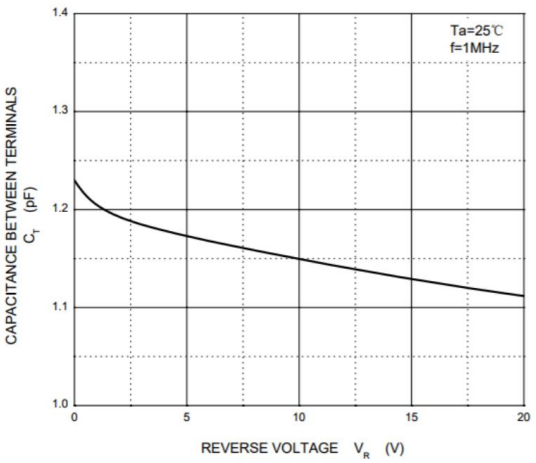
Forward Characteristics



Reverse Characteristics

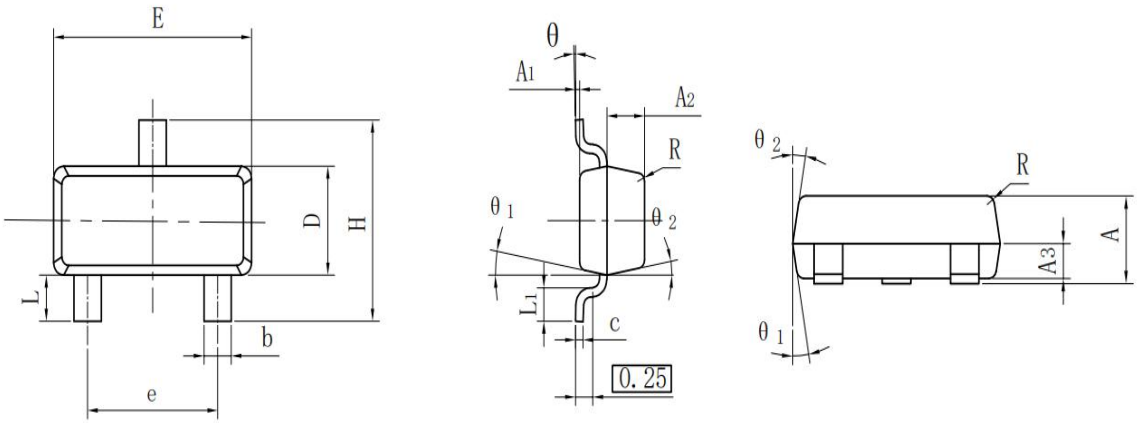


Power Derating Curve



CT vs VR

SOT-23 Package Information



SYMBOL	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.90	1.10	0.035	0.043
A1	0.02	0.10	0.001	0.004
A2	0.50	0.60	0.020	0.024
A3	0.35	0.45	0.014	0.018
b	0.37	0.50	0.015	0.020
c	0.09	0.18	0.004	0.007
D	1.20	1.40	0.047	0.055
E	2.80	3.04	0.110	0.120
e	1.80	2.00	0.071	0.079
L	0.45	0.60	0.018	0.024
L1	0.10	0.30	0.004	0.012
H	2.10	2.64	0.083	0.104
θ	0°	8°	0°	8°
θ1	7°	11°	7°	11°
θ2	8°	12°	8°	12°
R	0.12	0.15	0.005	0.006